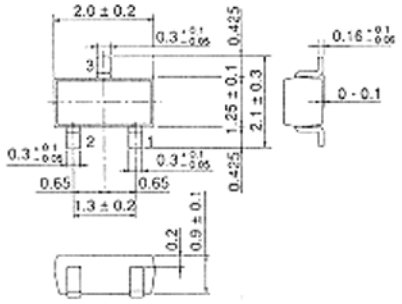
HITACHI

# 2SC4264

SILICON NPN EPITAXIAL

VHF/UHF RF AMPLIFIER, LOCAL OSCILLATOR, MIXER




(CMPAK)

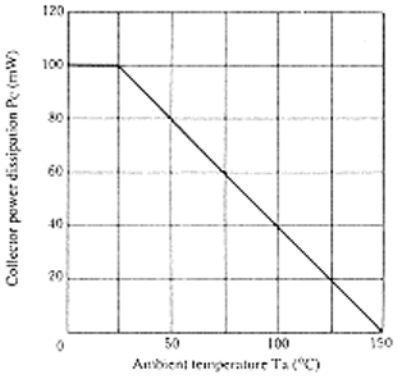
1. Emitter
2. Base
3. Collector

(Dimensions in mm)

## ■ ABSOLUTE MAXIMUM RATINGS (Ta=25°C)

| Item | Symbol | 2SC4264 | Unit |
|---|---|---|---|
| Collector to base voltage | $V_{CBO}$ | 20 | V |
| Collector to emitter voltage | $V_{CEO}$ | 11 | V |
| Emitter to base voltage | $V_{EBO}$ | 3 | V |
| Collector current | $I_C$ | 50 | mA |
| Collector power dissipation | $P_C$ | 100 | mW |
| Junction temperature | $T_j$ | 150 | °C |
| Storage temperature | $T_{stg}$ | −55 to +150 | °C |

**MAXIMUM COLLECTOR DISSIPATION CURVE**




## ■ ELECTRICAL CHARACTERISTICS (Ta=25°C)

| Item | Symbol | Test Condition | min. | typ. | max. | Unit |
|---|---|---|---|---|---|---|
| Collector to base breakdown voltage | $V_{(BR)CBO}$ | $I_C$ = 10μA, $I_E$ = 0 | 20 | — | — | V |
| Collector cutoff current | $I_{CBO}$ | $V_{CB}$ = 15V, $I_E$ = 0 | — | — | 0.5 | μA |
| | $I_{CEO}$ | $V_{CE}$ = 11V, $R_{BE}$ = ∞ | — | — | 10 | μA |
| Emitter cutoff current | $I_{EBO}$ | $V_{EB}$ = 3V, $I_C$ = 0 | — | — | 10 | μA |
| Collector to emitter saturation voltage | $V_{CE(sat)}$ | $I_C$ = 10mA, $I_B$ = 5mA | — | — | 0.7 | V |
| DC current transfer ratio | $h_{FE}$ | $V_{CE}$ = 10V, $I_C$ = 5mA | 20 | — | — | |
| Collector output capacitance | $C_{ob}$ | $V_{CB}$ = 10V, $I_E$ = 0, $f$ = 1MHz | — | — | 1.5 | pF |
| Gain bandwidth product | $f_T$ | $V_{CE}$ = 10V, $I_C$ = 10mA | 1.4 | — | — | GHz |

* Marking is [GC].

■ See characteristic curves of 2SC2734.